## 結晶 Si/PEDOT:PSS 太陽電池における界面局所電界強度の増強効果 Photovoltaic performance of PEDOT:PSS/c-Si junction solar cells by adding ferroelectric polymer thin-layer

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**1. Introduction:** We have investigated the effect of solution derived ferroelectric (FE) layer P(VDF-TrFE) on the front-PEDOT:PSS/Si junction solar cells. In particular, the open circuit voltage ( $V_{oc}$ ) corresponding to the built-in potential is increased from 525 mV to 531 mV by inserting the FE layer (~6 nm) between PEDOT:PSS/Si interface and farther improved to 561 mV by inserting FE at rear Si/cathode interface. In addition, the PCE is also enhanced from 9.83% to 11.53%.

**2. Experimental:** The solar cells are fabricated on n-Si (250 $\mu$ m thick 0.1~0.5  $\Omega$ -cm resistivity 1×1 cm<sup>2</sup>) substrate. After the RCA cleaning of the substrate, a thin layer (~6nm) of the FE polymer is spin coated (SC) on top or/and back side of the n-Si substrate followed by thermal annealing at 100°C for 10min. After that, a ~ 100-nm-thick PEDOT:PSS is coated and heat treated at 140 ° C for 30 min. Then, the upper Ag grid and the back Al electrodes are provided as anode and cathode.

**3. Results and discussion:** Fig. 1(a) shows the  $1/C^2$ –V characteristics of the PEDOT:PSS/n-Si interface together with FE layer insertion. The built-in potential ( $\psi_{bi}$ ) is determined by the linear extrapolation of the  $1/C^2$ –V graph. It's increased from 0.79 V to ~ 0.86 V by inserting ~6nm FE layer at cathode interface. The enhanced  $\psi_{bi}$  indicates the increasing of internal electric field provided by the spontaneous polarization of FE polymer. Fig. 1(b) shows *J*-V curves of the PEDOT:PSS/n-Si solar cells with and without FE layer. The induced electric field by FE layer contribute to improve carrier collection ability as well as V<sub>oc</sub> and PCE as observed in *J*-V characteristics. We will discuss the effect of bias poling and thermal annealing on photovoltaic performance.



Fig.1: (a) C-V and (b) J-V characteristics of the PEDOT:PSS/n-Si solar cell with and without FE layer.